30V，N 通道 NextFET™ 功率金属氧化物半导体场效应晶体管 (MOSFET)

查询样品: CSD17552Q5A

特性

- 超低栅极电荷 **(Qg)** 和栅漏电荷 **(Qgd)**
- 低热阻
- 雪崩级
- 无铅端子镀层
- 符合 **RoHS** 标准
- 无卤素
- 小外形尺寸无引线 **(SON) 5mm × 6mm** 塑料封装

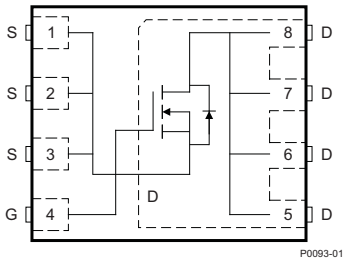
应用范围

- 网络互联、电信和计算系统中的负载点同步降压
- 为控制场效应晶体管 **(FET)** 应用进行了优化

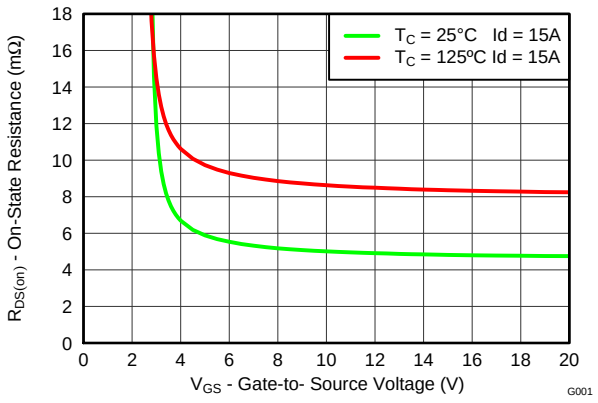
说明

NexFET™ 功率 MOSFET 被设计用于大大减少功率转换应用中的功率损失。

图 **1.** 顶视图



R_{DS}（接通）与 V_{GS}间的关系



产品概述

V_{DS}	漏源电压	30		V
Q_g	栅极电荷总量 (4.5V)	9.0		nC
Q_{gd}	栅漏栅极电荷	2.0		nC
R_{DS}（接通）	漏源导通电阻	V_{GS}=4.5V	6.1	mΩ
		V_{GS}=10V	5.1	mΩ
$V_{GS(th)}$	阀值电压	1.5		V

订购信息

器件	封装	介质	数量	出货
CSD17552Q5A	5mm x 6mm SON 塑料封装	13 英寸卷带	2500	卷带封装

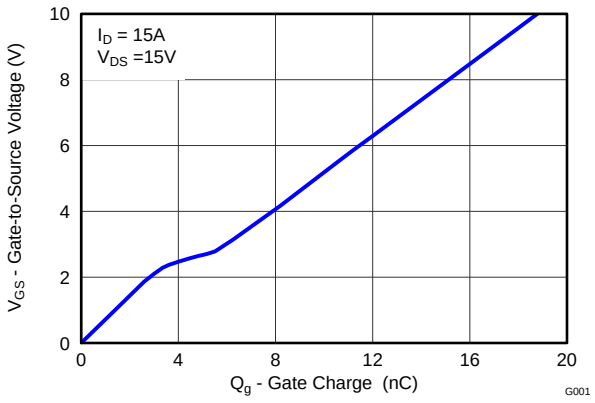
绝对最大额定值

T_A=25°C 时测得，除非另外注明		值	单位
V_{DS}	漏源电压	30	V
V_{GS}	栅源电压	±20	V
I_D	持续漏极电流，T_C = 25°C	60	A
	持续漏极电流，受芯片限制	88	A
	持续漏极电流，T_A=25°C 时测得(1)	17	A
I_{DM}	脉冲漏极电流，T_A=25°C 时测得(2)	106	A
P_D	功率耗散(1)	3.0	W
T_J, T_{STG}	运行结温和储存温度范围	-55 至 150	°C
E_{AS}	雪崩能量，单一脉冲 I_D=30A，L=0.1mH，R_G=25Ω	45	mJ

(1) $R_{\theta JA}$= 40°C/W，这是在一个厚度为 0.06 英寸 (1.52mm) 的 FR4 印刷电路板 (PCB) 上的 1 英寸^2(6.45cm^2)，2 盎司（厚度 0.071mm）的铜过渡垫片上测得的典型值。

(2) 脉冲持续时间 ≤ 300μs，占空比 ≤ 2%

栅极电荷



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

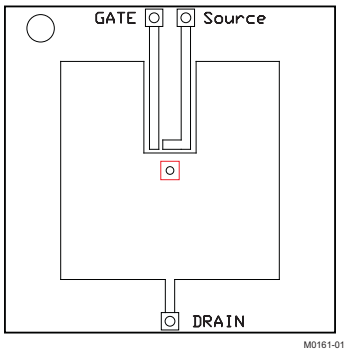
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = 250µA	30			V
I_{DSS}	Drain to Source Leakage Current	V_{GS} = 0V, V_{DS} = 24V			1	µA
I_{GSS}	Gate to Source Leakage Current	V_{DS} = 0V, V_{GS} = 20V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	1.1	1.5	1.9	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 4.5V, I_D = 15A		6.1	7.5	mΩ
		V_{GS} = 10V, I_D = 15A		5.1	6.2	mΩ
g_{fs}	Transconductance	V_{DS} = 15V, I_D = 15A		77		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		1580	2050	pF
C_{oss}	Output Capacitance			385	500	pF
C_{rss}	Reverse Transfer Capacitance			28	36	pF
R_G	Series Gate Resistance			0.9	1.8	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 15V, I_D = 15A		9.0	12	nC
Q_{gd}	Gate Charge Gate to Drain			2.0		nC
Q_{gs}	Gate Charge Gate to Source			3.6		nC
$Q_{g(th)}$	Gate Charge at Vth			2.1		nC
Q_{oss}	Output Charge	V_{DS} = 15V, V_{GS} = 0V		11		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 15V, V_{GS} = 4.5V, I_{DS} = 15A, R_G = 2Ω		7.6		ns
t_r	Rise Time			11.4		ns
$t_{d(off)}$	Turn Off Delay Time			12.2		ns
t_f	Fall Time			3.6		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_{SD} = 11A, V_{GS} = 0V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DS}= 13V, I_F = 15A, di/dt = 300A/µs		20		nC
t_{rr}	Reverse Recovery Time			18		ns

THERMAL CHARACTERISTICS

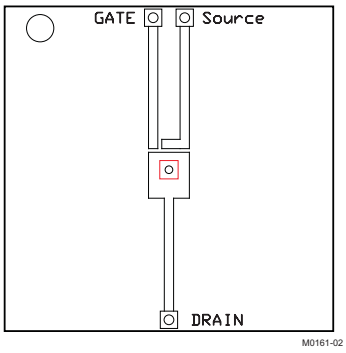
(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1)			1.8	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1)(2)			50	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 50°C/W when mounted on 1 inch^2 (6.45 cm^2) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 125°C/W when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

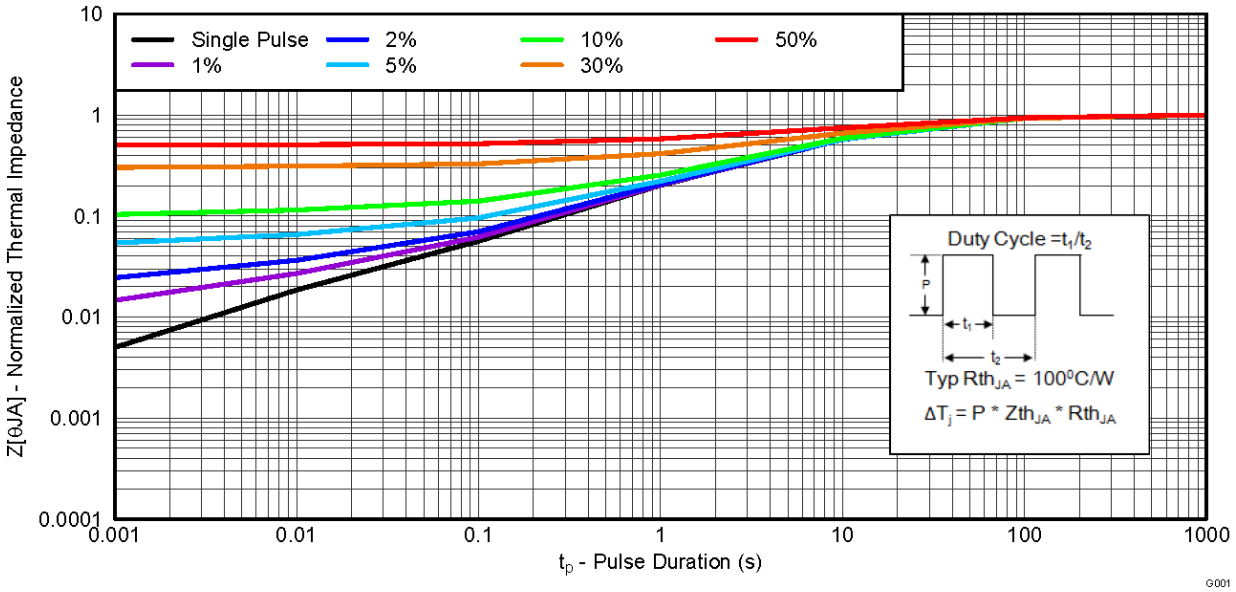


Figure 2. Transient Thermal Impedance

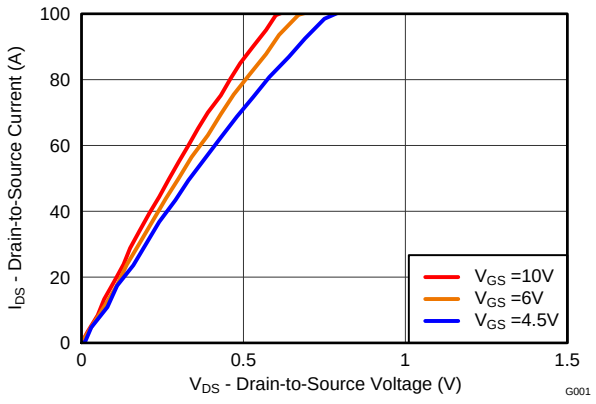


Figure 3. Saturation Characteristics

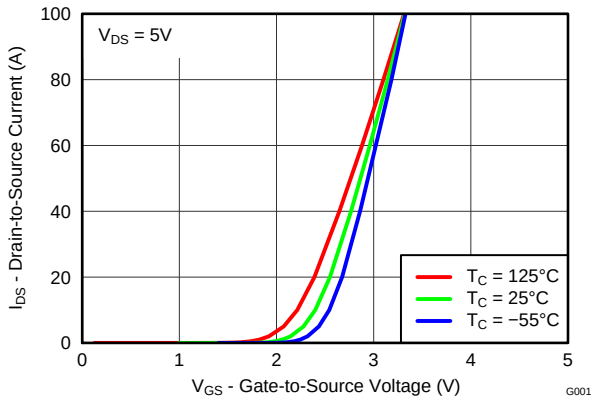


Figure 4. Transfer Characteristics

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

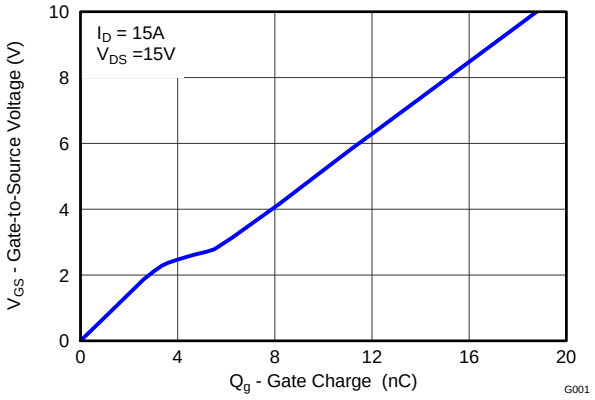


Figure 5. Gate Charge

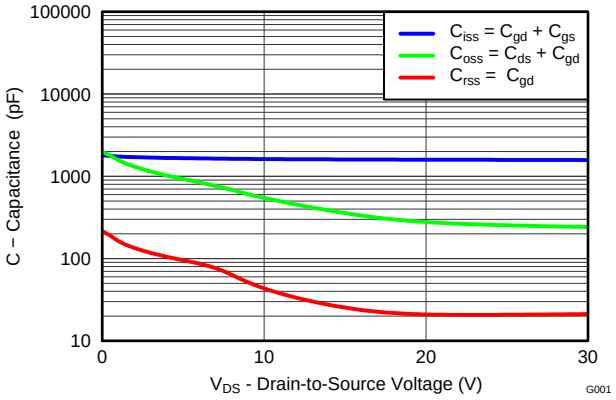


Figure 6. Capacitance

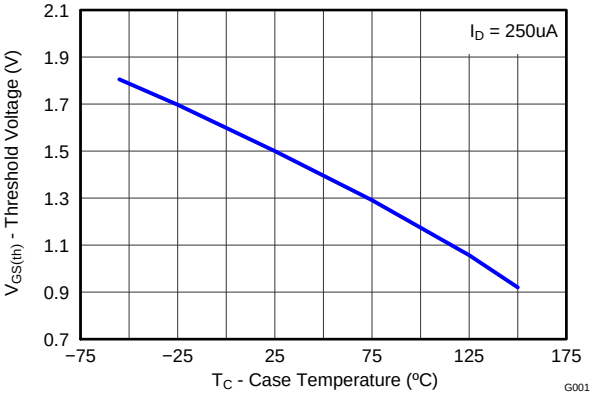


Figure 7. Threshold Voltage vs. Temperature

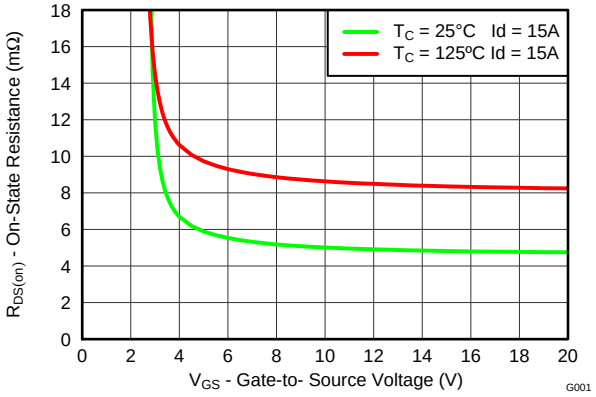


Figure 8. On-State Resistance vs. Gate-to-Source Voltage

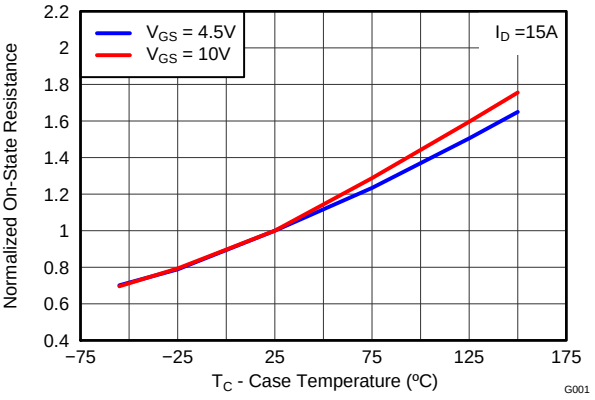


Figure 9. Normalized On-State Resistance vs. Temperature

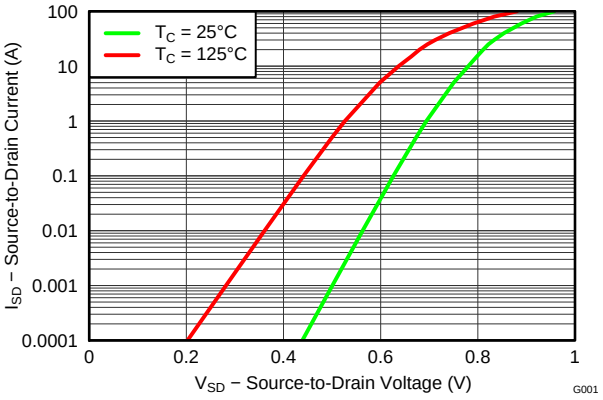


Figure 10. Typical Diode Forward Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

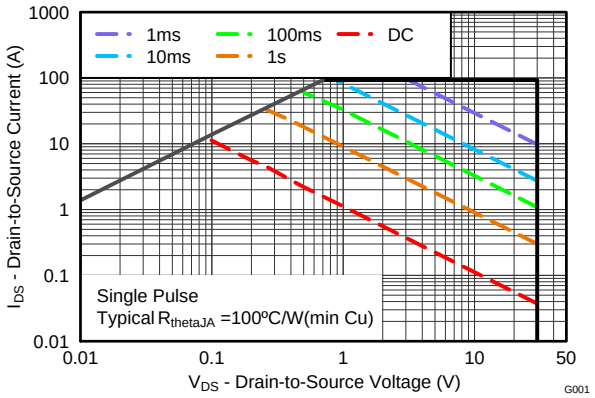


Figure 11. Maximum Safe Operating Area

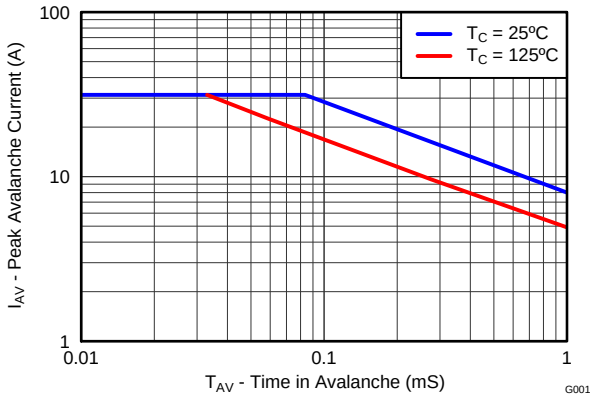


Figure 12. Single Pulse Unclamped Inductive Switching

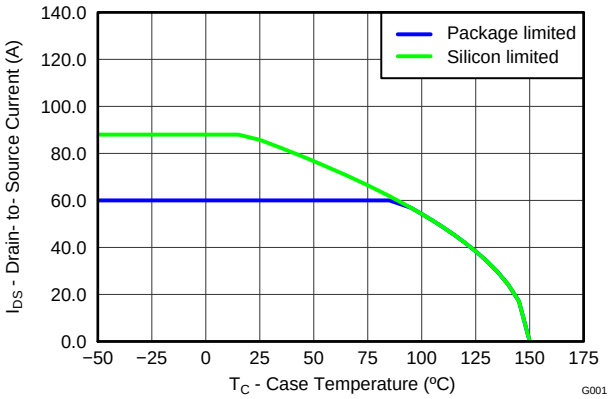
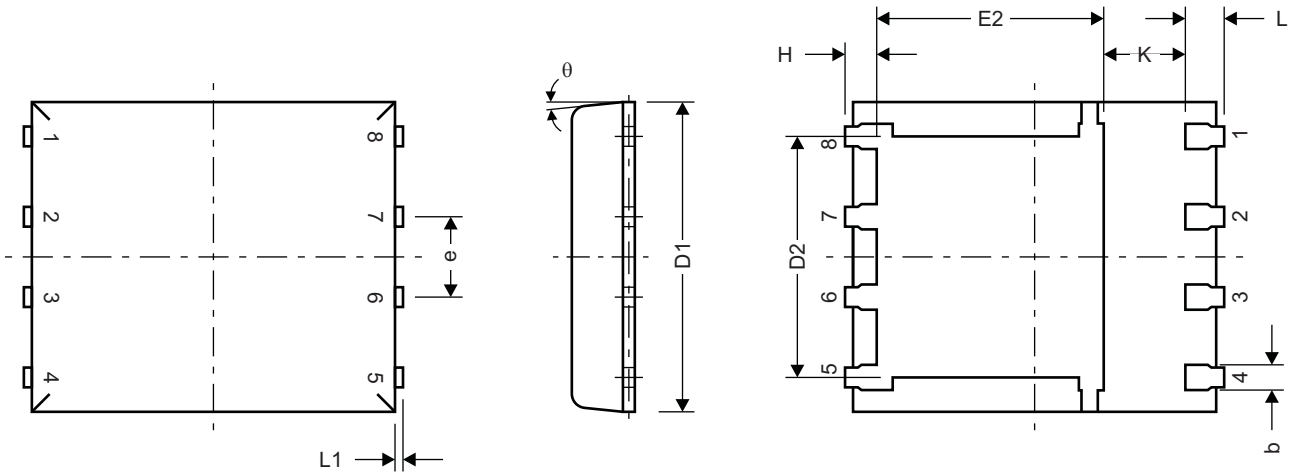
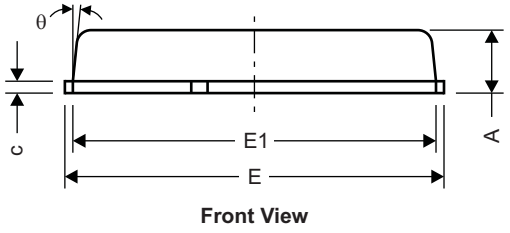


Figure 13. Maximum Drain Current vs. Temperature

MECHANICAL DATA

Q5A Package Dimensions

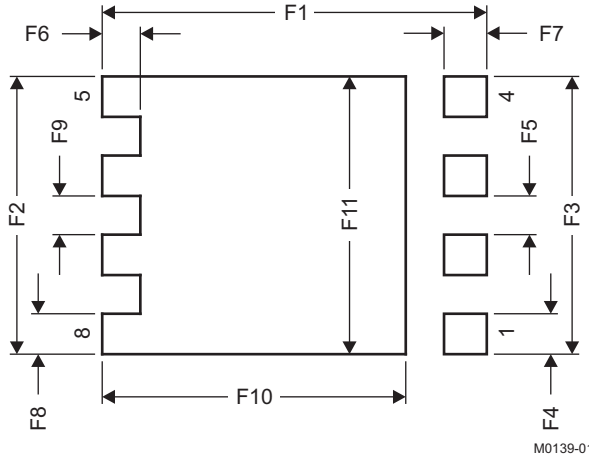




M0135-01

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.17	1.27	1.37
H	0.41	0.56	0.71
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°		12°

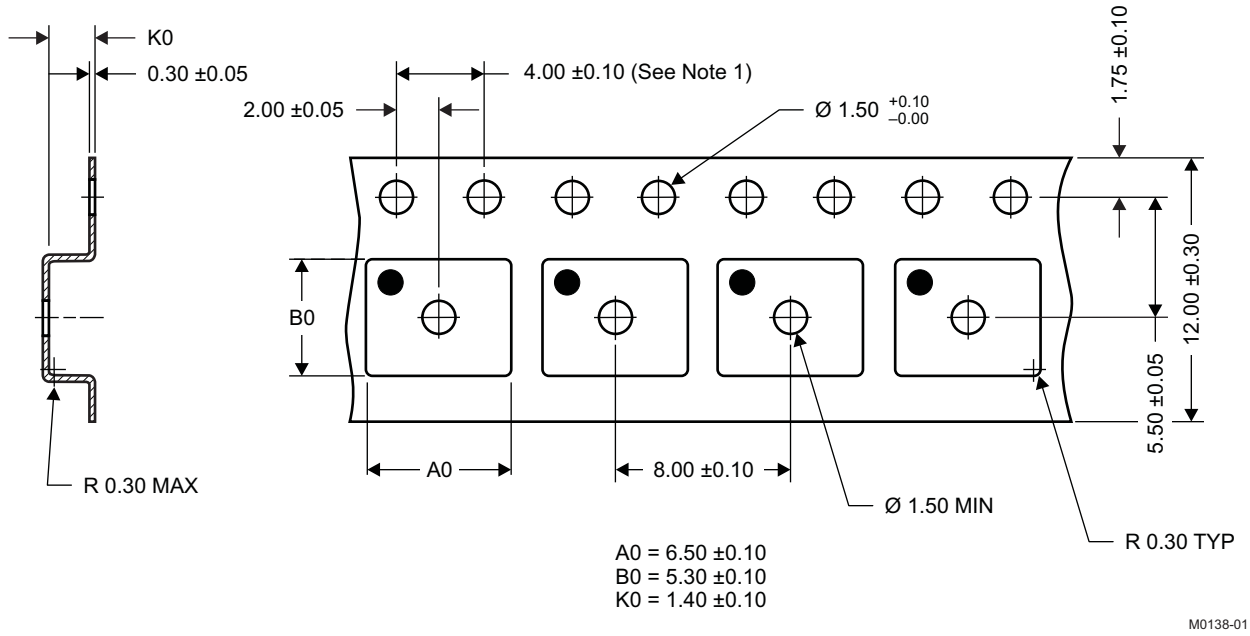
Figure 14. Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

Q5A Tape and Reel Information



Notes:

1. 10-sprocket hole-pitch cumulative tolerance ±0.2
2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified)
5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17552Q5A	ACTIVE	VSONP	DQJ	8	2500	RoHS-Exempt & Green	SN	Level-1-260C-UNLIM	-55 to 150	CSD17552	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

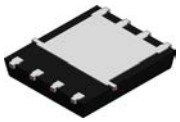
(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

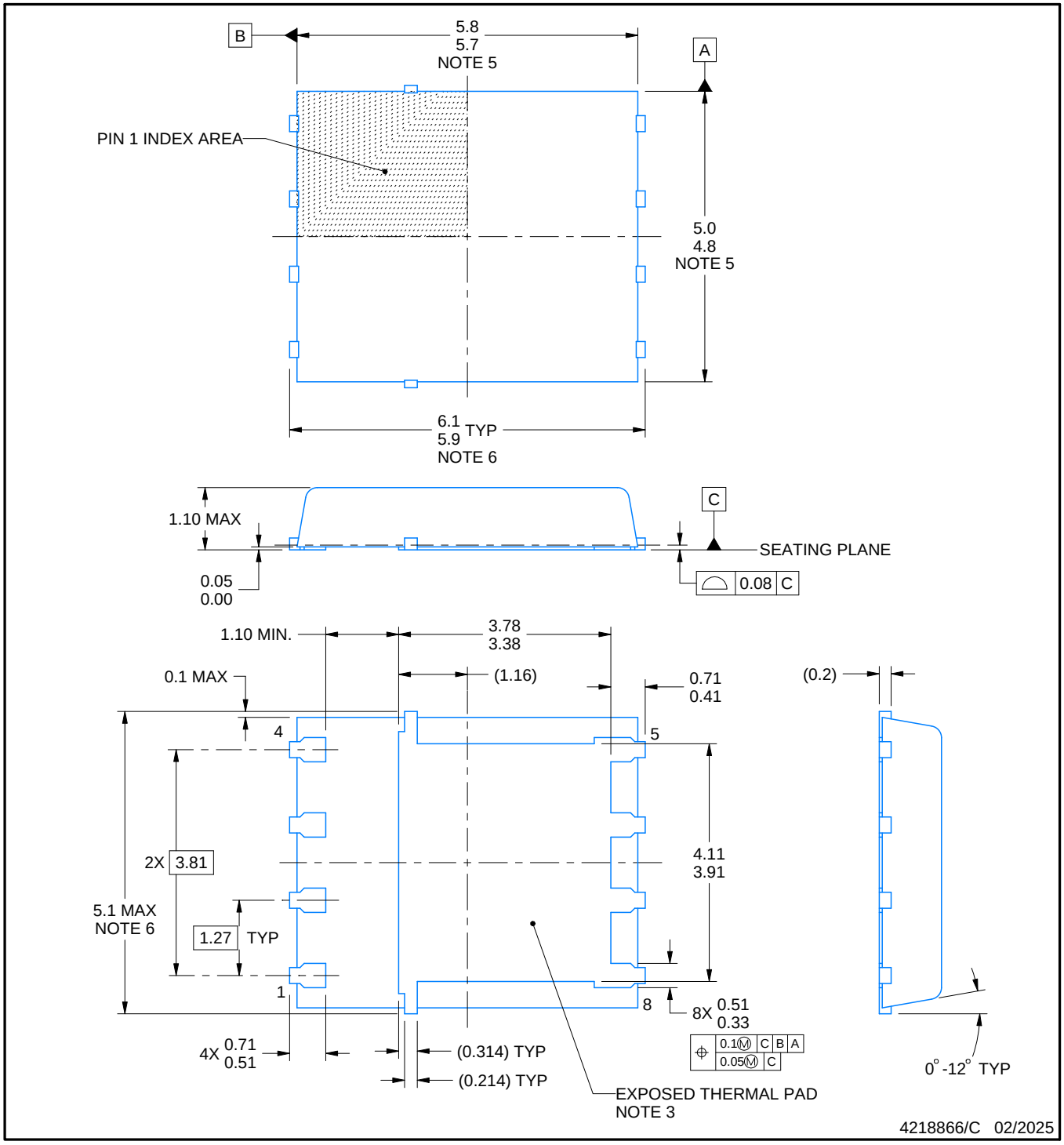


PACKAGE OUTLINE

DQJ0008A

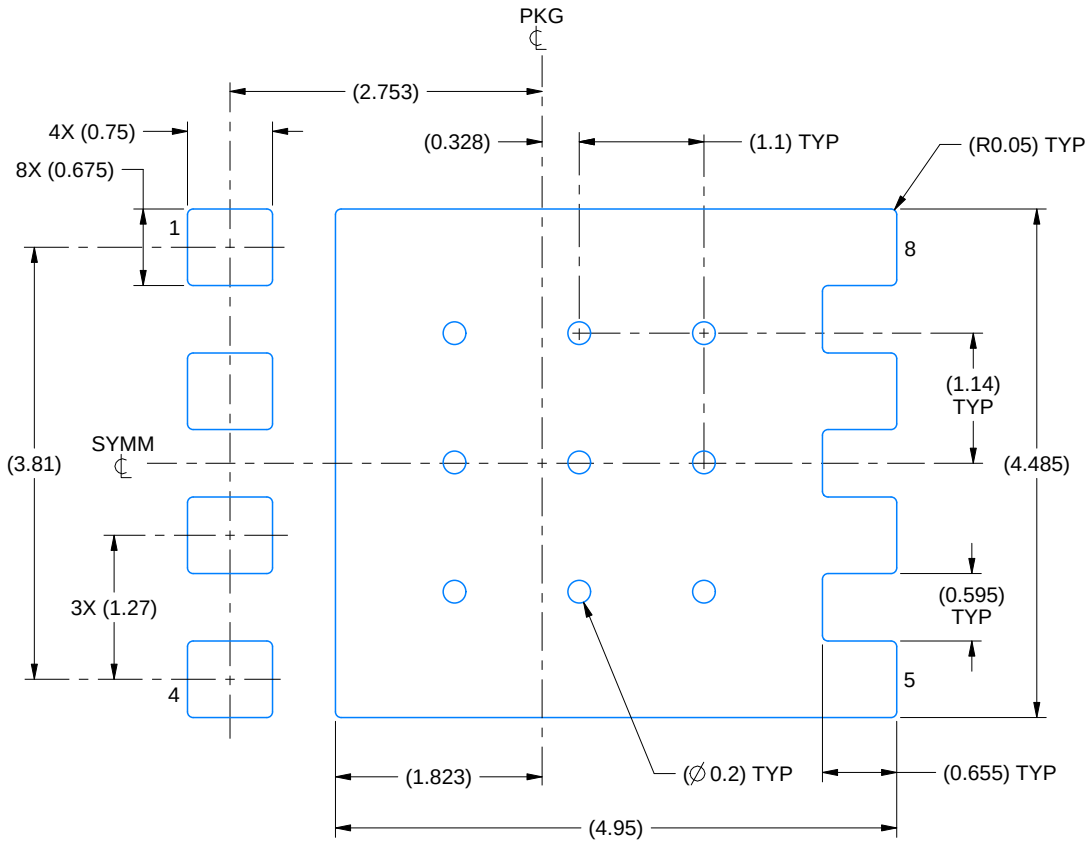
VSONP - 1.1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

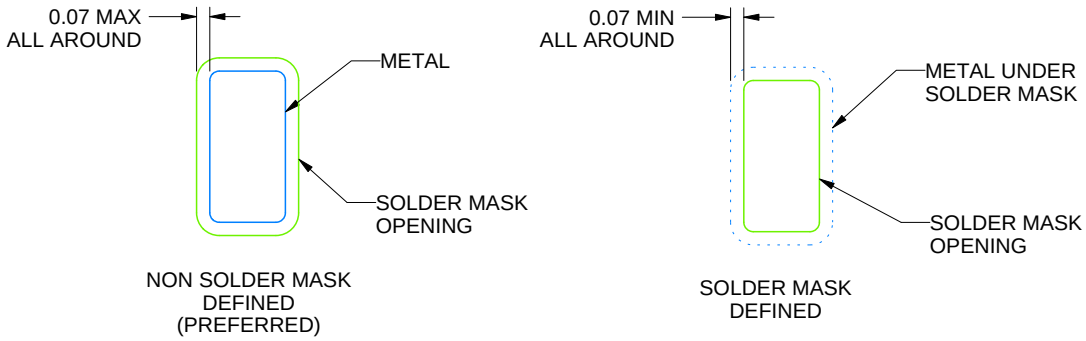


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
4. Metalized features are supplier options and may not be on the package.
5. These dimensions do not include mold flash protrusions or gate burrs.
6. These dimensions include interterminal flash or protrusion. Interterminal flash or protrusion shall not exceed 0.25 mm per side.



LAND PATTERN EXAMPLE
SOLDER MASK DEFINED
SCALE: 15X



SOLDER MASK DETAILS

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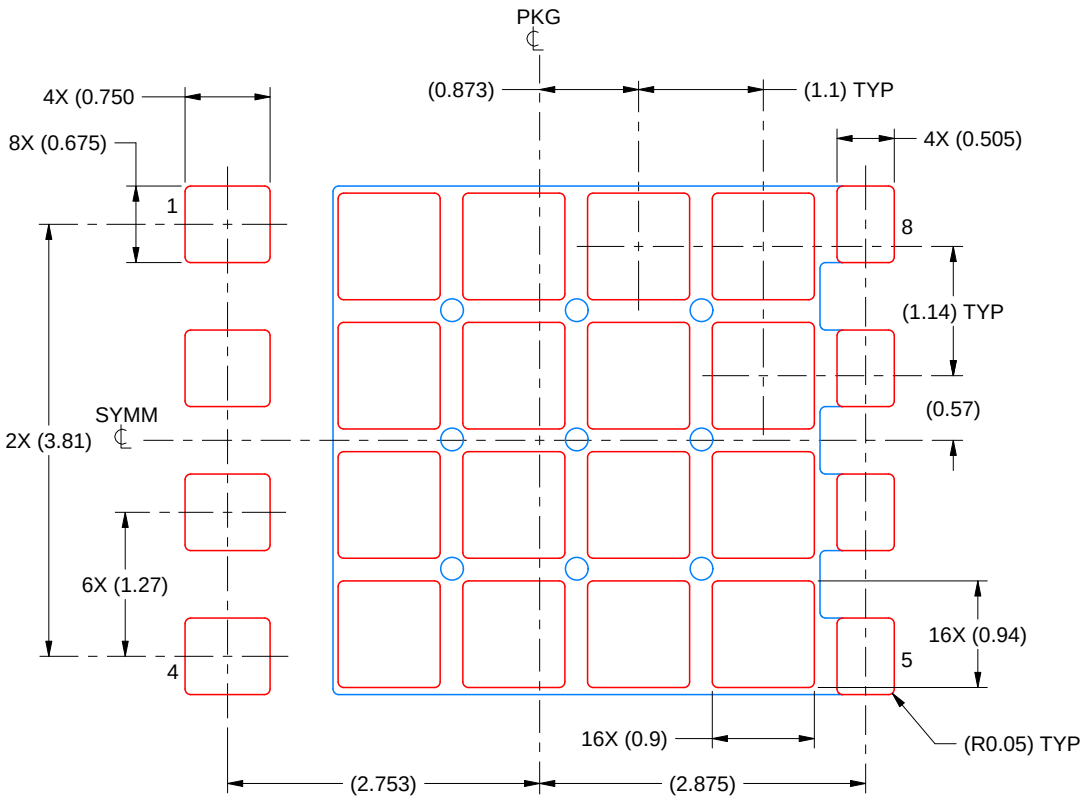
NOTES: (continued)

7. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
8. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD:
70% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE: 15X

4218866/C 02/2025

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要通知和免责声明

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